

Top View

Vishay Semiconductors

Small Signal Schottky Diodes, Single & Dual

Features

- These diodes feature very low turn-on voltage and fast switching
- These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges
- Space saving LLP package
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

Mechanical Data

Parts Table

Case: LLP75-3B Plastic case Molding Compound Flammability Rating: UL 94 V-0 Terminals: High temperature soldering guaranteed: 260 °C/4 x 10 sec. at terminals Weight: approx. 5.2 mg



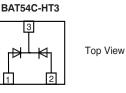


BAT54-HT3





BAT54S-HT3





Part	Ordering code	Type Marking	Remarks
BAT54-HT3	BAT54-HT3-GS08	L4	Tape and Reel
BAT54A-HT3	BAT54A-HT3-GS08	L5	Tape and Reel
BAT54C-HT3	BAT54C-HT3-GS08	L6	Tape and Reel
BAT54S-HT3	BAT54S-HT3-GS08	L7	Tape and Reel

17004

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit	
Repetitive peak reverse voltage=Working peak reverse voltage		V _{RRM}	30	V	
Forward continuous current		١ _F	200	mA	
Repetitive peak forward current		I _{FRM}	300	mA	
Surge forward current current		I _{FSM}	600	mA	
Power dissipation		P _{tot}	230	mW	

Thermal Characteristics

 $T_{amb} = 25 \ ^{\circ}C$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambiant air		R _{thJA}	430	K/W
Junction temperature		Tj	125	°C
Storage temperature range		T _{stg}	- 65 to + 150	°C

BAT54-HT3 to BAT54S-HT3

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Electrical Characteristics

 T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Reverse Breakdown voltage	100 μA pulses	V _(BR)	30			V
Leakage current	Pulse test t _p < 300 μ s, δ < 2 % at V _R = 25 V				2	μA
Forward voltage	I_{F} = 0.1 mA, t_{p} < 300 $\mu s,$ δ < 2 $\%$	V _F			240	mV
	I_F = 1 mA, t_p < 300 µs, δ < 2 %	V _F			320	mV
	I_{F} = 10 mA, t_{p} < 300 $\mu s,$ δ < 2 %	V _F			400	mV
	I_{F} = 30 mA, t_{p} < 300 µs, δ < 2 %	V _F			500	mV
	I_{F} = 100 mA, t_{p} < 300 $\mu s,$ δ < 2 %	V _F			800	mV
Diode capacitance	V _R = 0 V, f = 1 MHz	C _{tot}			12	pF
Reverse recovery time	$I_{\rm F}$ = 10 mA , $I_{\rm R}$ = 10 mA to $I_{\rm R}$ = 1 mA, $R_{\rm L}$ = 100 Ω	t _{rr}			5	ns

Typical Characteristics (Tamb = 25 °C unless otherwise specified)

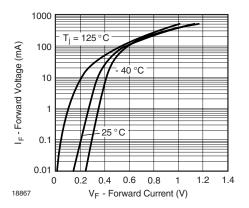


Figure 1. Typical Forward Voltage Forward Current at Various Temperatures

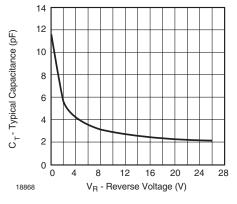
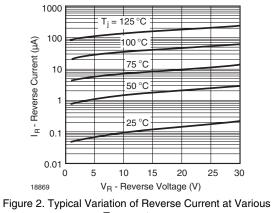


Figure 3. Typical Capacitance $^\circ\text{C}$ vs. Reverse Applied Voltage V_R

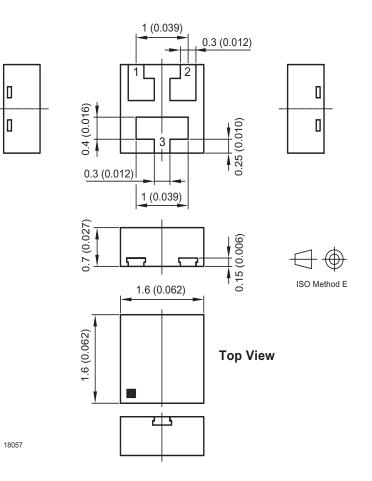


Temperatures



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Package Dimensions in mm (Inches)



BAT54-HT3 to BAT54S-HT3

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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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